

# General purpose transistors (dual transistors)

## EMX1 / UMX1N / IMX1

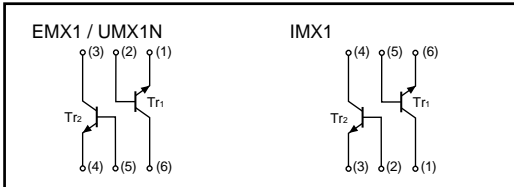
**●Features**

- 1) Two 2SC2412K chips in a EMT or UMT or SMT package.
- 2) Mounting possible with EMT3 or UMT3 or SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

**●Structure**

Epitaxial planar type  
NPN silicon transistor

**●Equivalent circuit**



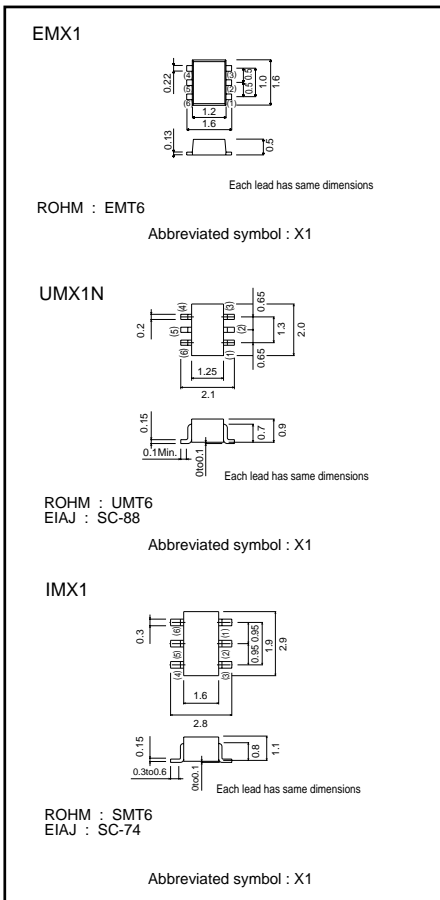
The following characteristics apply to both Tr1 and Tr2.

**●Absolute maximum ratings (Ta = 25°C)**

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	60	V
Collector-emitter voltage	V <sub>CE0</sub>	50	V
Emitter-base voltage	V <sub>EB0</sub>	7	V
Collector current	I <sub>c</sub>	150	mA
Power dissipation	EMX1, UMX1N	150 (TOTAL)	mW *1
	IMX1	300 (TOTAL)	mW *2
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

\*1 120mW per element must not be exceeded.  
\*2 200mW per element must not be exceeded.

**●External dimensions (Units : mm)**



Transistors

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	60	—	—	V	I <sub>c</sub> =50μA
Collector-emitter breakdown voltage	BV <sub>CE0</sub>	50	—	—	V	I <sub>c</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	7	—	—	V	I <sub>E</sub> =50μA
Collector cutoff current	I <sub>CB0</sub>	—	—	0.1	μA	V <sub>CB</sub> =60V
Emitter cutoff current	I <sub>EB0</sub>	—	—	0.1	μA	V <sub>EB</sub> =7V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	0.4	V	I <sub>c</sub> /I <sub>B</sub> =50mA/5mA
DC current transfer ratio	h <sub>FE</sub>	120	—	560	—	V <sub>CE</sub> =6V, I <sub>c</sub> =1mA
Transition frequency	f <sub>T</sub>	—	180	—	MHz	V <sub>CE</sub> =12V, I <sub>E</sub> =-2mA, f=100MHz *
Output capacitance	C <sub>ob</sub>	—	2	3.5	PF	V <sub>CB</sub> =12V, I <sub>E</sub> =0A, f=1MHz

●Packaging specifications

Type	Package	Taping		
	Code	T2R	TN	T110
	Basic ordering unit (pieces)	8000	3000	3000
EMX1	○	—	—	—
UMX1N	—	○	—	—
IMX1	—	—	—	○

●Electrical characteristic curves

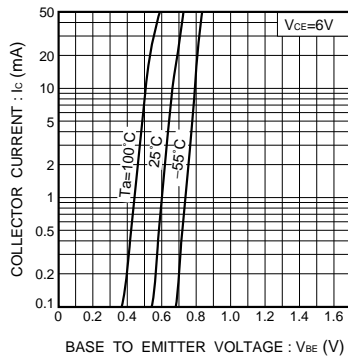


Fig.1 Grounded emitter propagation characteristics

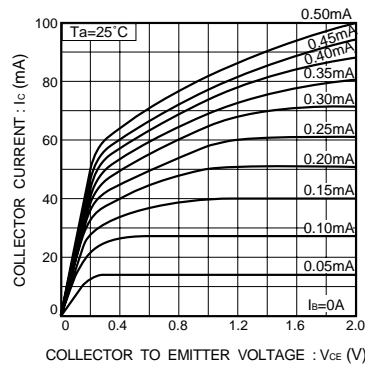


Fig.2 Grounded emitter output characteristics ( I )

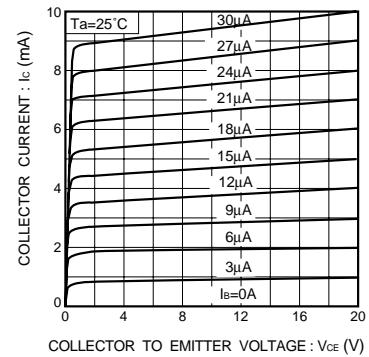


Fig.3 Grounded emitter output characteristics ( II )

Transistors

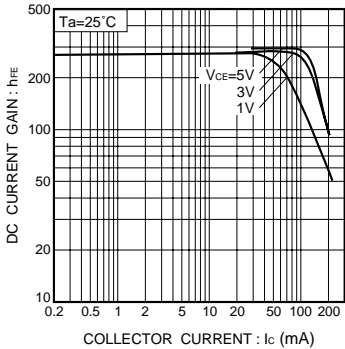


Fig.4 DC current gain vs. collector current ( I )

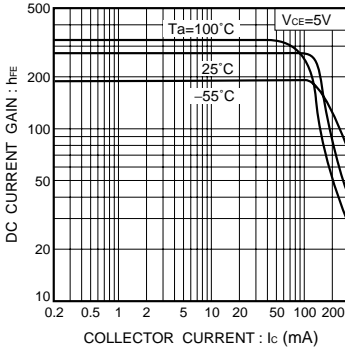


Fig.5 DC current gain vs. collector current ( II )

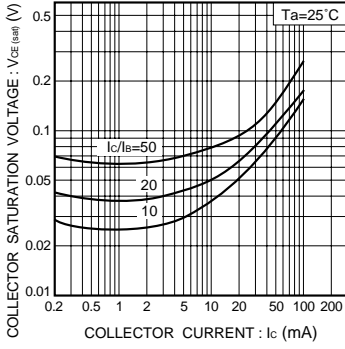


Fig.6 Collector-emitter saturation voltage vs. collector current

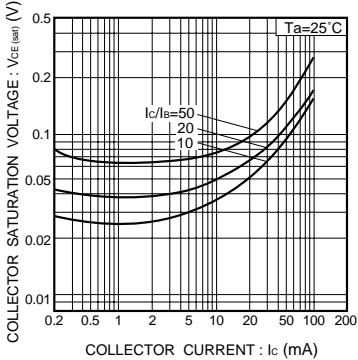


Fig.7 Collector-emitter saturation voltage vs. collector current ( I )

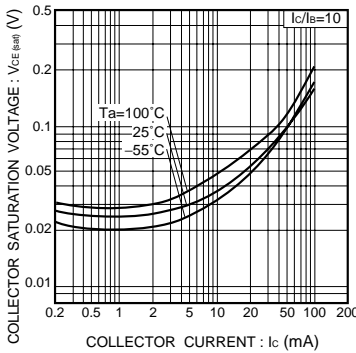


Fig.8 Collector-emitter saturation voltage vs. collector current ( II )

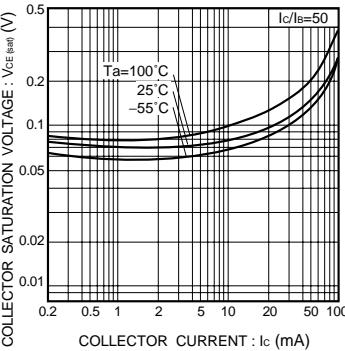


Fig.9 Collector-emitter saturation voltage vs. collector current ( III )

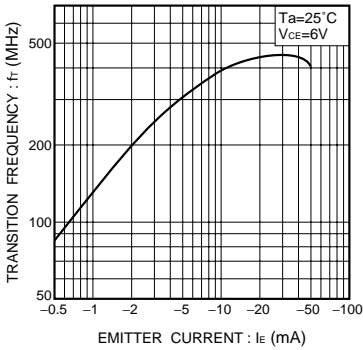


Fig.10 Gain bandwidth product vs. emitter current

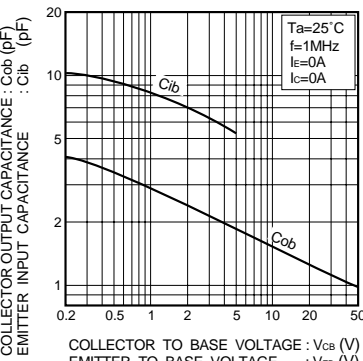


Fig.11 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

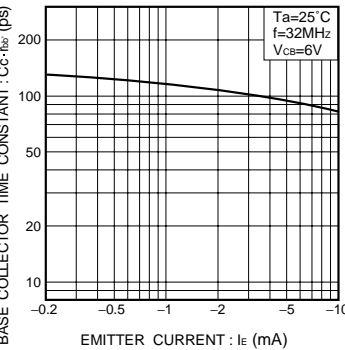


Fig.12 Base-collector time constant vs. emitter current

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